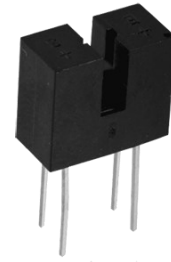


High Resolution Slotted Optical Switch

OPB847TX

Obsolete (OPB847TXV, OPB848TX, OPB848TXV)



Features:

- Non-contact switching
- Apertured for high resolution
- Hermetically sealed components
- TX devices processed to MIL-PRF-19500

Description:

The **OPB847TX** consist of a gallium aluminum arsenide LED and a silicon phototransistor, which is soldered into a printed PCBoard and then mounted in a high-temperature plastic housing on opposite sides of a 0.10 inch (2.54 mm) wide slot. Both device types have a 0.025 inch by 0.060 inch (0.635 mm by 1.524 mm) aperture in front of the phototransistor for high resolution positioning sensing. Phototransistor switching takes place when an opaque object passes through the slot.

TX device components are processed to OPTEK's military screening program patterned after MIL-PRF-19500.

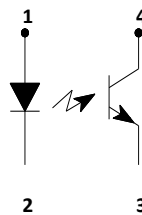
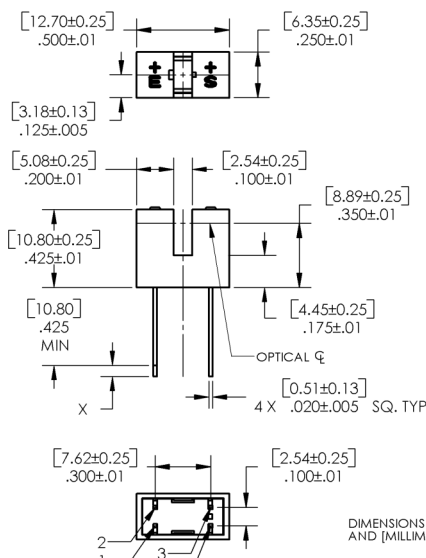
Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Contact your local representative or OPTEK for more information.

Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment safety
- Machine safety

Part Number	LED Peak Wavelength	Sensor	Slot Width / Depth	Aperture Emitter/Sensor	Lead Length / Spacing
OPB847TX	890 nm	Transistor	0.100" / 0.250"	0.025" / 0.025"	0.425" / 0.300"
OPB847TXV Obsolete					
OPB848TX Obsolete	890 nm	Transistor	0.100" / 0.250"	0.025" / 0.025"	0.425" / 0.300"
OPB848TXV Obsolete					



Pin #	Description
1	Anode
2	Cathode
3	Emitter
4	Collector

General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

High Resolution Slotted Optical Switch

OPB847TX

Obsolete (OPB847TXV, OPB848TX, OPB848TXV)



Electrical Specifications

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Operating Temperature Range	-65°C to $+125^\circ\text{C}$
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 seconds with soldering iron]	260°C

Input Diode

Forward DC Current	50 mA
Reverse Voltage	2 V
Power Dissipation ⁽²⁾	100 mW

Output Phototransistor

Collector-Emitter Voltage	50 V
Emitter-Collector Voltage	7 V
Power Dissipation ⁽²⁾	100 mW

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
--------	-----------	-----	-----	-----	-------	-----------------

Input Diode

V_F	Forward Voltage ⁽⁴⁾	1.00	1.35	1.70	V	$I_F = 20\text{ mA}$
		1.20	1.55	1.90		$I_F = 20\text{ mA}, T_A = -55^\circ\text{C}$
		0.80	1.20	1.60		$I_F = 20\text{ mA}, T_A = 100^\circ\text{C}$
I_R	Reverse Current	-	0.10	100	μA	$V_R = 2\text{ V}$

Output Phototransistor

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	50	110	-	V	$I_C = 1\text{ mA}, I_F = 0$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	7	10	-	V	$I_E = 100\text{ }\mu\text{A}, I_F = 0$
$I_{C(OFF)}$	Collector-Emitter Dark Current	-	0.20	100	nA	$V_{CE} = 10\text{ V}, I_F = 0$
		-	10	100	μA	$V_{CE} = 10\text{ V}, I_F = 0, T_A = 100^\circ\text{C}$

Notes:

- (1) Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly $1.00\text{ mW}/^\circ\text{C}$ above 25°C .
- (3) Methanol and isopropanol are recommended as cleaning agents.
- (4) Measurement is taken during the last $500\text{ }\mu\text{s}$ of a single 1.0 ms test pulse. Heating due to increased pulse rate or pulse width can cause change in measurement results.

General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

TT Electronics | OPTEK Technology
2900 E. Plano Pkwy, Plano, TX 75074 | Ph: +1 972 323 2200
www.ttelectronics.com | sensors@ttelectronics.com

High Resolution Slotted Optical Switch

OPB847TX

Obsolete (OPB847TXV, OPB848TX, OPB848TXV)



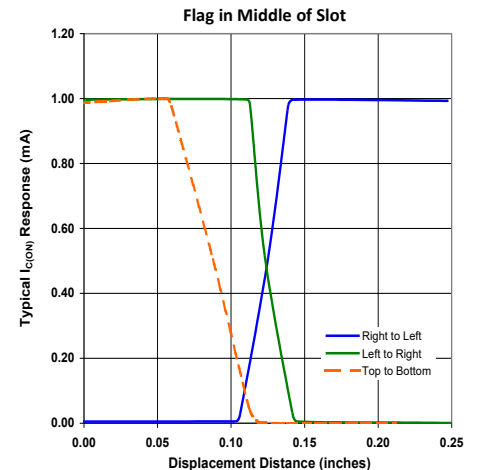
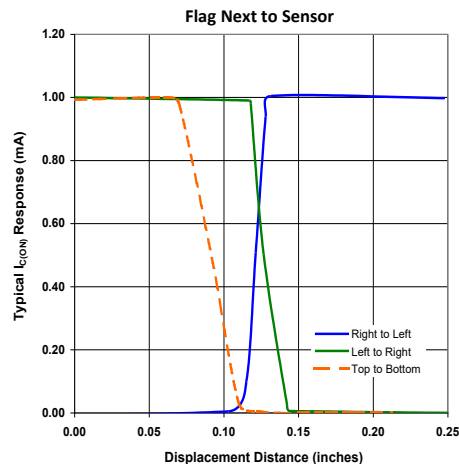
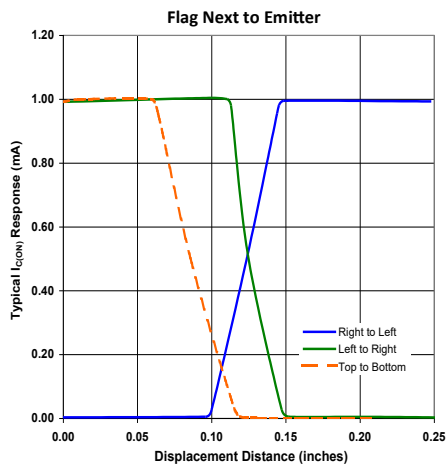
Electrical Specifications

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Combined						
$I_{C(ON)}$	On-State Collector Current ⁽¹⁾ OPB847TX OPB847TX OPB847TX	4.00 2.50 2.50	- - -	- - -	mA	$V_{CE} = 10\text{ V}$, $I_F = 20\text{ mA}$ $V_{CE} = 10\text{ V}$, $I_F = 20\text{ mA}$, $T_A = -55^\circ\text{C}$ $V_{CE} = 10\text{ V}$, $I_F = 20\text{ mA}$, $T_A = 100^\circ\text{C}$
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	-	0.20	0.30	V	$I_C = 2\text{ mA}$, $I_F = 20\text{ mA}$
t_r	Output Rise Time	-	12	20	μs	$V_{CC} = 10\text{ V}$, $I_F = 20\text{ mA}$, $R_L = 1000\Omega$
t_f	Output Fall Time	-	12	20		

Notes:

- (1) Measurement is taken during the last 500 μs of a single 1.0 ms test pulse. Heating due to increased pulse rate or pulse width can cause change in measurement results.



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.